

Search History (13 pp.) ~~4/2~~ (9/1/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2300	((257/192) or (257/194) or (257/195) or (257/285) or (257/590)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 12:59
L2	10	L1 and ("InAlN" "AlInN") and (piezo piezoelectric piezo-electric polari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:00
S1	5	"772673".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:14
S2	33	((("5,447,874") or ("5,471,077") or ("5,486,705") or ("5,493,136") or ("5,521,403") or ("5,521,404") or ("5,554,865") or ("5,596,211") or ("5,611,955") or ("5,652,440") or ("5,668,387") or ("5,696,387") or ("5,698,900") or ("5,739,558") or ("5,811,843") or ("5,811,844") or ("5,821,825") or ("5,831,277") or ("5,834,796") or ("5,847,414") or ("5,856,217") or ("5,880,491") or ("5,900,653") or ("5,929,467") or ("5,976,920") or ("6,049,091") or ("6,049,097") or ("6,057,566") or ("6,064,082") or ("6,100,542") or ("6,140,169") or ("6,177,685") or ("6,214,678"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/01/06 16:17
S3	16	((("6,232,624") or ("6,242,293") or ("6,242,766") or ("6,316,793") or ("6,355,951") or ("6,392,253") or ("6,429,467") or ("6,444,552") or ("6,465,289") or ("6,515,316") or ("6,524,899") or ("6,531,718") or ("6,583,454") or ("6,646,293") or ("6,727,531") or ("20010020700"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/01/06 16:19
S4	4	JP-2000223697\$-\$\$.did. JP-2001196575\$-\$\$.did. wo-0059084\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:29
S5	0	wo-000059084\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:24

S6	1	wo-200059084\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:21
S7	0	(2001/0020700).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:30
S8	2	("20010020700").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:31
S9	54	S2 S3 S4 S5 S6 S7 S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:32
S10	1645	hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 17:38
S11	1	hemt.ti,ab,clm. and barrier adj layer near4 (AIInN "In.sub."\$3"Al. sub."\$3"N" "Al.sub."\$3"In.sub. "\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 17:39
S12	1	hemt.ti,ab,clm. and barrier adj layer near4 (AIInN InAIN "In.sub. "\$3"Al.sub."\$3"N" "Al.sub."\$3"In. sub."\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 17:40
S13	1	(high adj mobility adj electron adj transistor hemt).ti,ab,clm. and barrier adj layer near4 (AIInN InAIN "In.sub."\$3"Al.sub."\$3"N" "Al.sub."\$3"In.sub."\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 17:40
S14	1	(high adj mobility adj electron adj transistor hemt).ti,ab,clm. and (separat\$3 barrier) adj layer near4 (AIInN InAIN "In.sub."\$3"Al.sub. "\$3"N" "Al.sub."\$3"In.sub."\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 17:41
S15	1	(high adj mobility adj electron adj transistor hemt).ti,ab,clm. and (separat\$3 barrier) adj (layer film) near4 (AIInN InAIN "In.sub."\$3"Al. sub."\$3"N" "Al.sub."\$3"In.sub. "\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 17:41

S16	54	(US-20010020700-\$).did. or (US-6214678-\$ or US-6177685-\$ or US-6140169-\$ or US-6064082-\$ or US-6100542-\$ or US-6057566-\$ or US-6049091-\$ or US-6049097-\$ or US-5976920-\$ or US-5900653-\$ or US-5929467-\$ or US-5880491-\$ or US-5856217-\$ or US-5834796-\$ or US-5847414-\$ or US-5831277-\$ or US-5811844-\$ or US-5821825-\$ or US-5811843-\$ or US-5698900-\$ or US-5739558-\$ or US-5696387-\$ or US-5652440-\$ or US-5668387-\$ or US-5611955-\$ or US-5596211-\$).did. or (US-5521404-\$ or US-5554865-\$ or US-5521403-\$ or US-5486705-\$ or US-5493136-\$ or US-5471077-\$ or US-5447874-\$ or US-6727531-\$ or US-6646293-\$ or US-6583454-\$ or US-6524899-\$ or US-6531718-\$ or US-6515316-\$ or US-6465289-\$ or US-6429467-\$ or US-6444552-\$ or US-6392253-\$ or US-6355951-\$ or US-6242766-\$ or US-6316793-\$ or US-6242293-\$ or US-6232624-\$).did. or (JP-2000223697-\$ or JP-2001196575-\$).did. or (JP-2001196575-\$ or JP-2000223697-\$ or WO-200059084-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/01/06 17:56
S17	1	(US-20040155260-\$).did.	US-PGPUB	OR	OFF	2005/01/07 09:47
S18	15	(high adj electron adj mobility adj transistor hemt).ti. and "257"/\$7. ccls.	US-PGPUB	OR	OFF	2005/01/07 09:48
S19	93	(high adj electron adj mobility adj transistor hemt).ti. and "257"/\$7. ccls.	US-PGPUB; USPAT	OR	OFF	2005/01/07 09:50
S20	1035	(257/194).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:57
S21	1	S20 and (InAlN "In.sub."\$3"Al. sub."\$3"N" "Al.sub."\$3"In.sub. "\$3"N") and charge adj density	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 09:54

S22	5	S20 and (InAlN "In.sub."\$3"Al.sub."\$3"N" "Al.sub."\$3"In.sub."\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:23
S23	1	S20 and (InAlN "In.sub."\$3"Al.sub."\$3"N" "Al.sub."\$3"In.sub."\$3"N") and (QW quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:24
S24	3	S20 and (InAlN "In.sub."\$3"Al.sub."\$3"N" "Al.sub."\$3"In.sub."\$3"N") and (2DEG Q2DEG two-dimensional adj electron adj gas two-dimensional adj Fermi adj gas QW quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:44
S25	9	(hemt high adj electron adj mobility adj transistor) and (InAlN "In.sub."\$3"Al.sub."\$3"N" "Al.sub."\$3"In.sub."\$3"N") and (2DEG Q2DEG two-dimensional adj electron adj gas two-dimensional adj Fermi adj gas QW quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 11:00
S26	2	(hemt high adj electron adj mobility adj transistor) and (InAlN "In.sub."\$3"Al.sub."\$3"N" "Al.sub."\$3"In.sub."\$3"N") near6 (barrier separating separation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 11:36
S27	62	(hemt high adj electron adj mobility adj transistor) and (AlGaIn "Al.sub."\$3"Gd.sub."\$3"N" "Ga.sub."\$3"Al.sub."\$3"N") near6 (barrier separating separation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 11:40
S28	19	(hemt high adj electron adj mobility adj transistor) and (AlGaIn "Al.sub."\$3"Gd.sub."\$3"N" "Ga.sub."\$3"Al.sub."\$3"N") near6 (barrier separating separation) and (QW quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:56
S29	22	portable adj telephone.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:57
S30	48	low adj noise adj amplifier.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:54

S31	27	radar.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:57
S32	20	sensor.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 16:09
S33	2	direct adj broadcast adj satellite.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S34	1	S29 and S30 and S31 and S32 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S35	1	S29 and S30 and S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S36	1	S29 and S30 and S31	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S37	1	S29 and S30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S38	1	S30 and S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:55
S39	5	S30 and S31	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:55
S40	8	"intermediate frequency amplifier" and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 16:45

S41	0	"intermediate frequency amplifier" and (intermediate adj amplifier) and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 16:46
S42	8	"intermediate frequency amplifier" and (intermediate adj2 amplifier) and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 16:48
S43	8	"intermediate frequency amplifier" and (intermediate adj2 amplifier IF adj amplifier) and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 16:49
S44	9	(intermediate adj2 amplifier IF adj amplifier) and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 17:52
S45	4	hemt.ti,ab,clm. and InGaN near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:02
S46	1	hemt.ti,ab,clm. and InAlN near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:03
S47	1	hemt.ti,ab,clm. and ("In.sub. "\$4"Al.sub."\$4"N" "In.sub."\$4"Al. sub."\$4"N") near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:04
S48	0	("(highadjelectronadjmobilityadjtra nsistorhemt).ti."):PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:58
S49	936	(high adj electron adj mobility adj transistor hemt).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:58
S50	51	(high adj electron adj mobility adj transistor hemt).ti. and GaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:59

S51	2078	((257/192) or (257/194) or (257/195) or (438/285) or (438/590)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 15:02
S52	1685	S51 and (high electron adj mobility adj transistor hemt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 15:03
S53	159	S51 and (high electron adj mobility adj transistor hemt) and GaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 15:05
S54	7	S51 and (high electron adj mobility adj transistor hemt) and GaN and InAlN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 15:07
S55	1	S51 and (high electron adj mobility adj transistor hemt) and GaN and InAlN near8 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 15:10
S56	71	((("3,764,865") or ("3,767,984") or ("3,855,690") or ("3,861,024") or ("3,943,622") or ("4,030,942") or ("4,075,652") or ("4,157,556") or ("4,163,984") or ("4,173,764") or ("4,325,181") or ("4,424,525") or ("4,593,301") or ("4,642,879") or ("4,714,948") or ("4,912,451") or ("4,961,194") or ("4,980,731") or ("5,021,857") or ("5,041,393") or ("5,084,743") or ("5,153,682") or ("5,180,681") or ("5,192,987") or ("5,262,660") or ("5,288,654") or ("5,312,765") or ("5,352,909") or ("5,358,878") or ("5,359,220") or ("5,365,080") or ("5,411,914"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 15:10
S57	0	("jp-8186450\$-\$\$.did.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 15:29
S58	2	jp-08186450\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 15:39

S59	141	(US-20010002048-\$ or US-20010020700-\$ or US-20010023964-\$ or US-20020058349-\$ or US-20040004223-\$ or US-20040026701-\$ or US-20040124435-\$ or US-20040155260-\$ or US-20040185643-\$).did. or (US-5447874-\$ or US-5471077-\$ or US-5486705-\$ or US-5493136-\$ or US-5521403-\$ or US-5521404-\$ or US-5554865-\$ or US-5596211-\$ or US-5611955-\$ or US-5652440-\$ or US-5668387-\$ or US-5696387-\$ or US-5698900-\$ or US-5739558-\$ or US-5811843-\$ or US-5811844-\$ or US-5821825-\$ or US-5831277-\$ or US-5834796-\$ or US-5847414-\$ or US-5856217-\$ or US-5880491-\$ or US-5900653-\$ or US-5929467-\$ or US-5976920-\$ or US-6049091-\$).did. or (US-6049097-\$ or US-6057566-\$ or US-6064082-\$ or US-6100542-\$ or US-6140169-\$ or US-6172382-\$ or US-6177685-\$ or US-6214678-\$ or US-6232624-\$ or US-6242293-\$ or US-6242766-\$ or US-6316793-\$ or US-6355951-\$ or US-6392253-\$ or US-6429467-\$ or US-6444552-\$ or US-6465289-\$ or US-6515316-\$ or US-6524899-\$ or US-6531718-\$ or US-6583454-\$ or US-6646293-\$ or US-6677619-\$ or US-6727531-\$ or US-6787820-\$ or US-5411914-\$ or US-5365080-\$).did. or (US-5359220-\$ or US-5358878-\$ or US-5352909-\$ or US-5312765-\$ or US-5288654-\$ or US-5262660-\$ or US-5192987-\$ or US-5180681-\$ or US-5153682-\$ or US-5084743-\$ or US-5041393-\$ or US-5021857-\$ or US-4980731-\$ or US-4961194-\$ or US-4912451-\$ or US-4714948-\$ or US-4642879-\$ or US-4593301-\$ or US-4424525-\$ or US-4325181-\$ or US-4173764-\$ or US-4163984-\$ or US-4157556-\$ or US-4075652-\$ or US-4030942-\$ or US-3943622-\$ or US-3861024-\$).did. or (US-3855690-\$ or US-3767984-\$ or US-3764865-\$).did. or (DE-4325181-\$ or DE-4424525-\$). did. or (JP-2000223697-\$ or JP-2001196575-\$ or JP-08186450-\$).did. or (EP-606776-\$ or US-5554865-\$ or JP-2000223697-\$ or WO-200058884-\$ or US-2000000000-\$)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/01/08 15:40
-----	-----	--	---	----	-----	------------------

S60	1	S59 and white.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 15:41
S61	3	polari?ation-induced near4 electric adj field and (InGaN "In.sub. "\$4"Ga.sub."\$4N "In.sub."\$4 near1 "Ga.sub."\$4 near1 N) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/31 13:43
S62	4	polari?ation-induced near4 electric adj field and (InGaN "In.sub. "\$4"Ga.sub."\$4N "In.sub."\$4 near1 "Ga.sub."\$4 near1 N) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:50
S65	63	(2DEG 2QDEG) and (polar piezo-electric piezoelectric piezo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:58
S66	63	(2DEG 2QDEG) and (polar piezo-electric piezoelectric piezo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:53
S67	51	(2DEG 2QDEG) and (polar piezo-electric piezoelectric piezo) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:59
S68	51	(2DEG 2QDEG) and (polar piezo-electric piezoelectric piezo piezo-FET) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:00
S75	0	piezo-fet and InGaN near8 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:10
S76	38	(piezo piezo-electric piezoelectric piezo-fet polarization adj induced polarization-induced) and InGaN near8 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:01
S77	7	(US-20050170574-\$ or US-20040108500-\$ or US-20040031437-\$ or US-20040023427-\$ or US-20020036287-\$ or US-20020017696-\$).did. or (US-6841809-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/08/31 14:22

S78	4	("6592663").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/31 14:57
S79	1	(2DEG 2QDEG) and (polar piezo-electric piezoelectric piezo piezo-FET) and transistor and (InAlN "INAlN/"\$5 AlInN "GaInN"\$5) and barrier near10 InGaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:59
S80	2	(2DEG 2QDEG) and (polar piezo-electric piezoelectric piezo piezo-FET) and transistor and (InAlN "INAlN/"\$5 AlInN "AlInN"\$5) and barrier near10 (InAlN AlInN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:00
S81	3	(piezo piezo-electric piezoelectric piezo-fet polarization adj induced polarization-induced) and (AlInN InAlN) near8 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:09
S82	0	(tensile adj strained tensile-strained) near4 (InAlN InAlN) near20 (GaIn near4 channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:41
S83	0	(tensile adj strained tensile-strained) near4 (InAlN InAlN (indium near1 alumin\$um) adj nitride) near20 (GaIn near4 channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:42
S84	75	(piezoelectric piezo-electric piezo adj electric) near6 (QW quantum adj "well")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:43
S85	3	(piezoelectric piezo-electric piezo adj electric) near6 (QW quantum adj "well") and (InAlN AlInN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:45
S86	0	("AlInN/GaN" "InAlN/GaN") near4 (QW QWs quantum adj ("well" "wells"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:47
S87	2	(InAlN AlInN) near4 (QW QWs quantum adj ("well" "wells"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:47

S88	23	(InAlN AlInN) near20 (QW QWs quantum adj ("well" "wells"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:47
S89	1	(InAlN AlInN) near20 (QW QWs quantum adj ("well" "wells")) and (piezo-electric piezoelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:48
S90	1	(InAlN AlInN "InAlN/InGaN" "AlInN/InGaN" "InAlN/GaInN") near20 (QW QWs quantum adj ("well" "wells")) and (piezo-electric piezoelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:51
S91	1	(InAlN AlInN "InAlN/InGaN" "AlInN/InGaN" "InAlN/GaInN") near20 (QW QWs quantum adj ("well" "wells")) and (piezo-electric piezoelectric piezo-FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:51
S92	1	(InAlN AlInN "InAlN/InGaN" "AlInN/InGaN" "InAlN/GaInN") near20 (QW QWs quantum adj ("well" "wells")) and (piezo-electric piezoelectric piezo-FET polari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:52
S93	1	(InAlN AlInN "InAlN/InGaN" "AlInN/InGaN" "InAlN/GaInN") near20 (MQW QW QWs quantum adj ("well" "wells")) and (piezo-electric piezoelectric piezo-FET polari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:52
S94	1436	nucleation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 07:38
S95	83	nucleation adj layer and (polari\$ation polari\$ed)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 07:38
S96	24	nucleation adj layer and (polari\$ation polari\$ed) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 07:40

S97	0	nucleation adj layer.ti. and (polarisation polarised) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 07:40
S98	115	nucleation adj layer.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 07:40
S99	6	nucleation adj layer.ti. and mobility	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 08:00
S100	38	"AlGaIn/GaN" and nucleation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 08:01
S101	0	"InAlIn/GaN" and nucleation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 08:01
S102	0	"AlInN/GaN" and nucleation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 08:01
S103	0	("AlInN/GaN" "InAlIn/GaN") and nucleation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 08:02
S104	0	("AlInN/GaN" "InAlIn/GaN") and (piezo-electric piezo-FET piezoelectric piezo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 08:02
S105	0	("AlInN/GaN" "InAlIn/GaN") and (piezo-electric piezo-FET piezoelectric piezo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 08:02
S106	0	("AlInN/GaN" "InAlIn/GaN") and (piezo-electric piezo-FET piezoelectric piezo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 08:02

S10 7	0	("AlInN/GaN" "InAlN/GaN") and (piezo-electric piezo-FET piezoelectric piezo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 08:02
S10 8	0	("AlInN/GaN" "InAlN/GaN") and nucleation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 08:06
S10 9	114	(polarization piezo piezoelectric piezo-electric piezo-FET) and nucleation adj (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 09:41
S11 0	2	("6727531"):PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 10:12